12-BIT TO 24-BIT MULTIPLEXED D-TYPE LATCH WITH 3-STATE OUTPUTS

SCAS570H – MARCH 1996 – REVISED JUNE 1999

- Member of the Texas Instruments *Widebus*™ Family
- *EPIC* ™ (Enhanced-Performance Implanted CMOS) Submicron Process
- B-Port Outputs Have Equivalent 26-Ω Series Resistors, So No External Resistors Are Required
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Thin-Shrink Small-Outline (DGG) and Plastic Shrink Small-Outline (DL) Packages

NOTE: For tape and reel order entry:
The DGGR package is abbreviated to GR.

DGG OR DL PACKAGE
(TOP VIEW)

Pin name	Pin	Pin	Pin name
$\overline{OEA}$	1	56	$\overline{OE2B}$
LE1B	2	55	LEA2B
2B3	3	54	2B4
GND	4	53	GND
2B2	5	52	2B5
2B1	6	51	2B6
V_{CC}	7	50	V_{CC}
A1	8	49	2B7
A2	9	48	2B8
A3	10	47	2B9
GND	11	46	GND
A4	12	45	2B10
A5	13	44	2B11
A6	14	43	2B12
A7	15	42	1B12
A8	16	41	1B11
A9	17	40	1B10
GND	18	39	GND
A10	19	38	1B9
A11	20	37	1B8
A12	21	36	1B7
V_{CC}	22	35	V_{CC}
1B1	23	34	1B6
1B2	24	33	1B5
GND	25	32	GND
1B3	26	31	1B4
LE2B	27	30	LEA1B
SEL	28	29	$\overline{OE1B}$

description

This 12-bit to 24-bit multiplexed D-type latch is designed for 1.65-V to 3.6-V_{CC} operation.

The SN74ALVCH162260 is used in applications in which two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and/or demultiplexing address and data information in microprocessor or bus-interface applications. This device also is useful in memory-interleaving applications.

Three 12-bit I/O ports (A1–A12, 1B1–1B12, and 2B1–2B12) are available for address and/or data transfer. The output-enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction.

Address and/or data information can be stored using the internal storage latches. The latch-enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch-enable input is high, the latch is transparent. When the latch-enable input goes low, the data present at the inputs is latched and remains latched until the latch-enable input is returned high.

The B outputs, which are designed to sink up to 12 mA, include equivalent 26-Ω resistors to reduce overshoot and undershoot.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

description (continued)

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH162260 is characterized for operation from –40°C to 85°C.

Function Tables

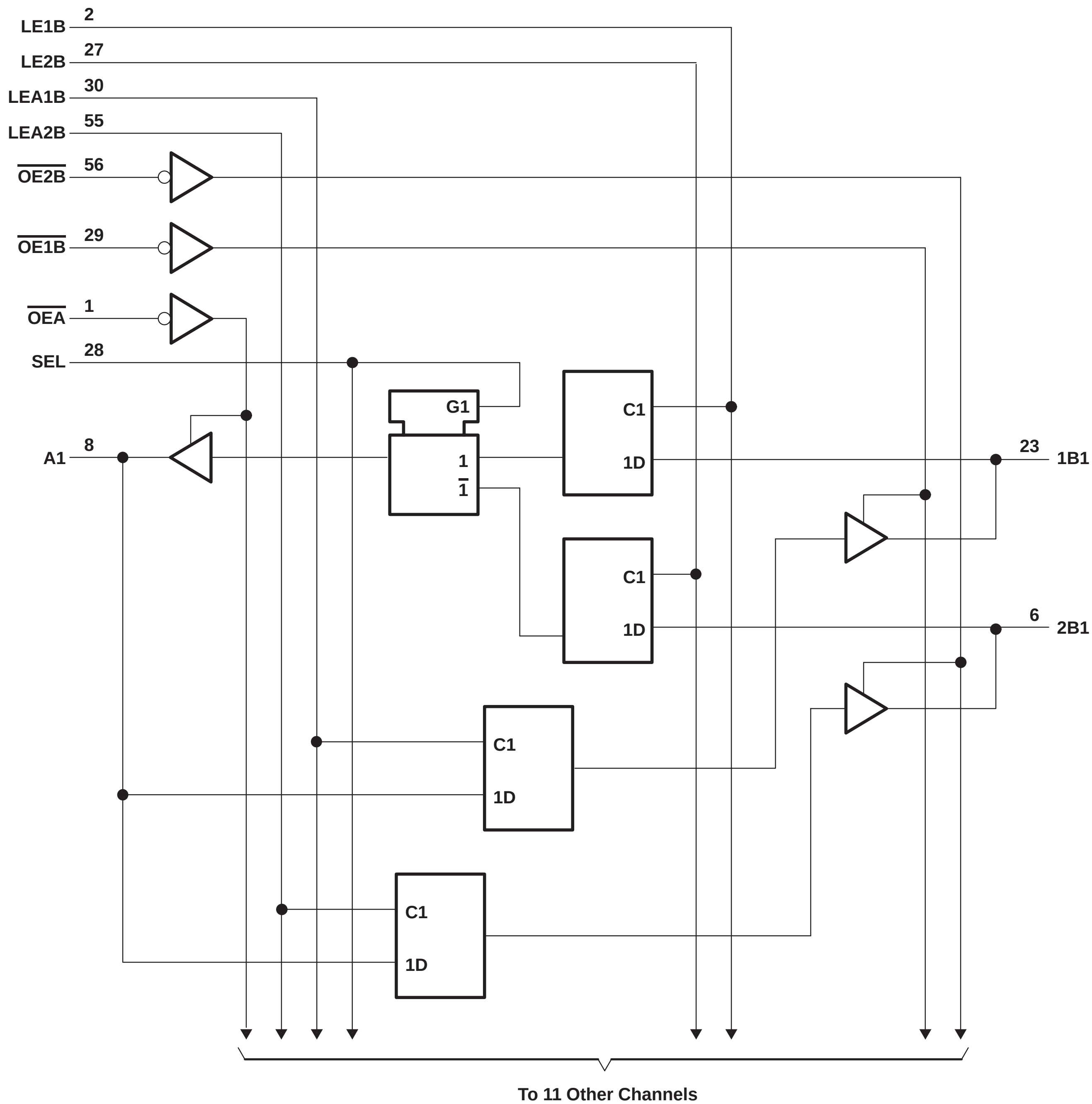
B TO A
($\overline{OEB}$ = H)

INPUTS						OUTPUT
1B	2B	SEL	LE1B	LE2B	$\overline{OEA}$	A
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0
X	X	X	X	X	H	Z

A TO B
($\overline{OEA}$ = H)

INPUTS					OUTPUTS	
A	LEA1B	LEA2B	$\overline{OE1B}$	$\overline{OE2B}$	1B	2B
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$
L	H	L	L	L	L	$2B_0$
H	L	H	L	L	$1B_0$	H
L	L	H	L	L	$1B_0$	L
X	L	L	L	L	$1B_0$	$2B_0$
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}		–0.5 V to 4.6 V
Input voltage range, V_I:	Except I/O ports (see Note 1)	–0.5 V to 4.6 V
	I/O ports (see Notes 1 and 2)	–0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2)		–0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)		–50 mA
Output clamp current, I_{OK} ($V_O < 0$)		–50 mA
Continuous output current, I_O		±50 mA
Continuous current through each V_{CC} or GND		±100 mA
Package thermal impedance, θ_{JA} (see Note 3):	DGG package	81°C/W
	DGV package	86°C/W
	DL package	74°C/W
Storage temperature range, T_{stg}		–65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

				MIN	MAX	UNIT
V_{CC}	Supply voltage			1.65	3.6	V
V_{IH}	High-level input voltage		V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$		V
			V_{CC} = 2.3 V to 2.7 V	1.7		
			V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage		V_{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	V
			V_{CC} = 2.3 V to 2.7 V		0.7	
			V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage			0	V_{CC}	V
V_O	Output voltage			0	V_{CC}	V
I_{OH}	High-level output current (A port)		V_{CC} = 1.65 V		–4	mA
			V_{CC} = 2.3 V		–12	
			V_{CC} = 2.7 V		–12	
			V_{CC} = 3 V		–24	
	High-level output current (B port)		V_{CC} = 1.65 V		–2	
			V_{CC} = 2.3 V		–6	
			V_{CC} = 2.7 V		–8	
			V_{CC} = 3 V		–12	
I_{OL}	Low-level output current (A port)		V_{CC} = 1.65 V		4	mA
			V_{CC} = 2.3 V		12	
			V_{CC} = 2.7 V		12	
			V_{CC} = 3 V		24	
	Low-level output current (B port)		V_{CC} = 1.65 V		2	
			V_{CC} = 2.3 V		6	
			V_{CC} = 2.7 V		8	
			V_{CC} = 3 V		12	
$\Delta t/\Delta v$	Input transition rise or fall rate				10	ns/V
T_A	Operating free-air temperature			–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	A port	I_{OH} = –100 µA		1.65 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA		1.65 V	1.2			
		I_{OH} = –6 mA		2.3 V	2			
		I_{OH} = –12 mA		2.3 V	1.7			
				2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2			
	B port	I_{OH} = –100 µA		1.65 V to 3.6 V	V_{CC}–0.2			
		I_{OH} = –2 mA		1.65 V	1.2			
		I_{OH} = –4 mA		2.3 V	1.9			
		I_{OH} = –6 mA		2.3 V	1.7			
				3 V	2.4			
		I_{OH} = –8 mA		2.7 V	2			
		I_{OH} = –12 mA		3 V	2			
V_{OL}	A port	I_{OL} = 100 µA		1.65 V to 3.6 V			0.2	V
		I_{OL} = 4 mA		1.65 V			0.45	
		I_{OL} = 6 mA		2.3 V			0.4	
		I_{OL} = 12 mA		2.3 V			0.7	
				2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
	B port	I_{OL} = 100 µA		1.65 V to 3.6 V			0.2	
		I_{OL} = 2 mA		1.65 V			0.45	
		I_{OL} = 4 mA		2.3 V			0.4	
		I_{OL} = 6 mA		2.3 V			0.55	
				3 V			0.55	
		I_{OL} = 8 mA		2.7 V			0.6	
		I_{OL} = 12 mA		3 V			0.8	
I_I		V_I = V_{CC} or GND		3.6 V			±5	µA
$I_{I(hold)}$		V_I = 0.58 V		1.65 V	25			µA
		V_I = 1.07 V			–25			
		V_I = 0.7 V		2.3 V	45			
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	µA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	µA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		3.5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		4.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

		V_{CC} = 1.8 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		†		150		150		150	MHz
t_w	Pulse duration, LE1B, LE2B, LEA1B, or LEA2B high	†		3.3		3.3		3.3		ns
t_{su}	Setup time, data before LE1B, LE2B, LEA1B, or LEA2B, high or low	†		1.4		1.1		1.1		ns
t_h	Hold time, data after LE1B, LE2B, LEA1B, or LEA2B, high or low	†		1.6		1.9		1.5		ns

† This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			†		150		150		150		MHz
t_{pd}	A	B		†	1	5.9		5.8	1.2	4.9	ns
	B	A		†	1	5.7		5.1	1.2	4.3	
	LE	A		†	1	5.6		5.2	1	4.4	
		B		†	1	6.1		5.9	1	5	
	SEL	A		†	1	6.9		6.6	1.1	5.6	
t_{en}	$\overline{OE}$	A		†	1	6.7		6.4	1	5.4	ns
		B		†	1	7.2		7.1	1	6	
t_{dis}	$\overline{OE}$	A		†	1	5.7		5	1.3	4.6	ns
		B		†	1	6.2		5.5	1.3	5.1	

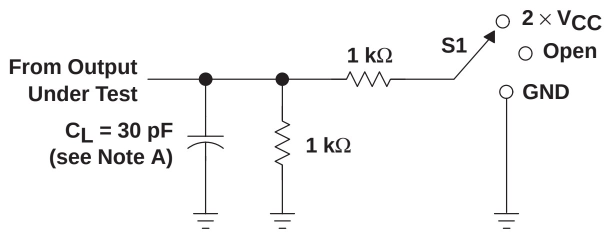
† This information was not available at the time of publication.

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	UNIT
				TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	All outputs enabled	C_L = 50 pF, f = 10 MHz	†	37	41	pF
		All outputs disabled		†	4	7	

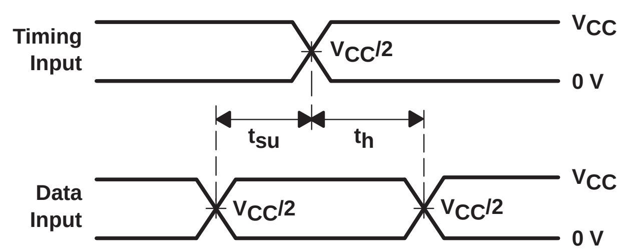
† This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.8 V

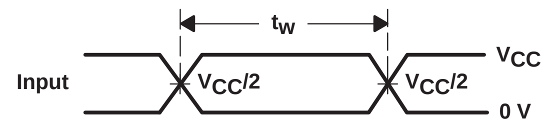


LOAD CIRCUIT

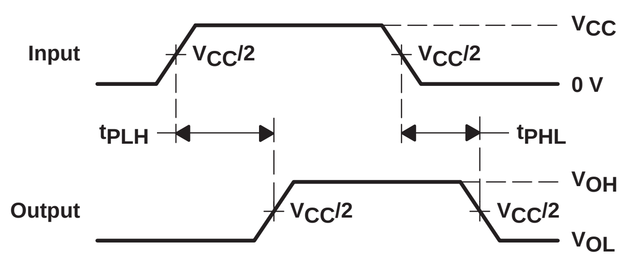
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



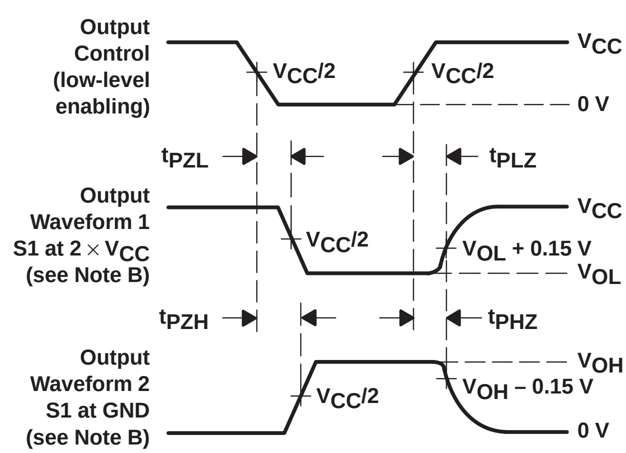
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

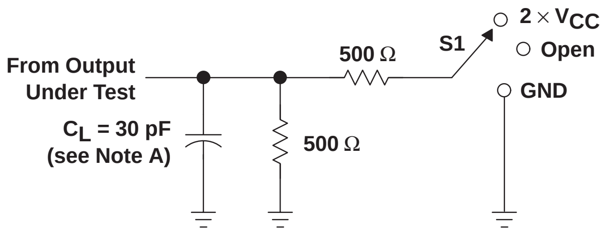


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

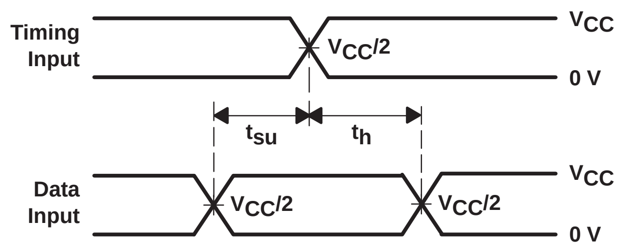
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

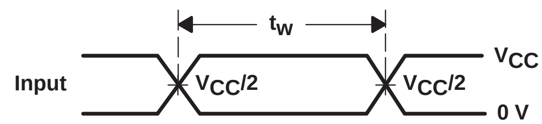


LOAD CIRCUIT

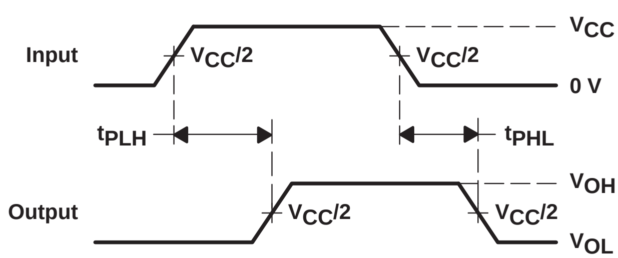
TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND



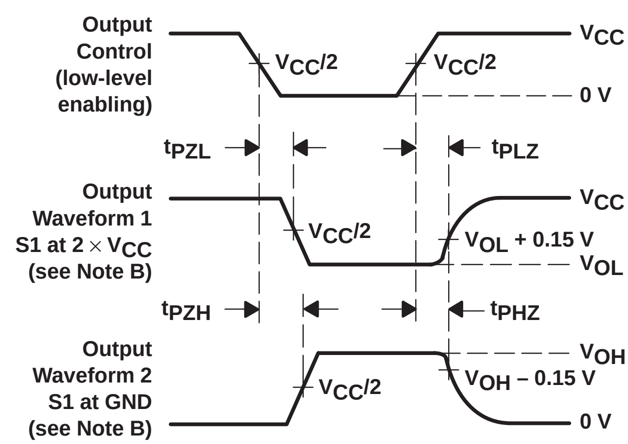
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

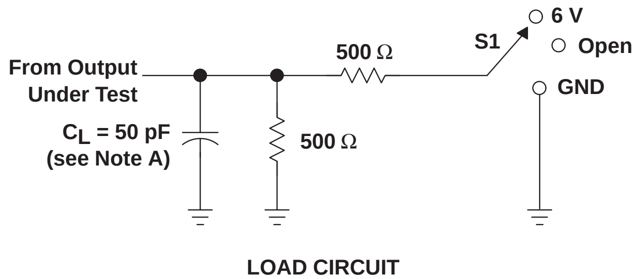


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

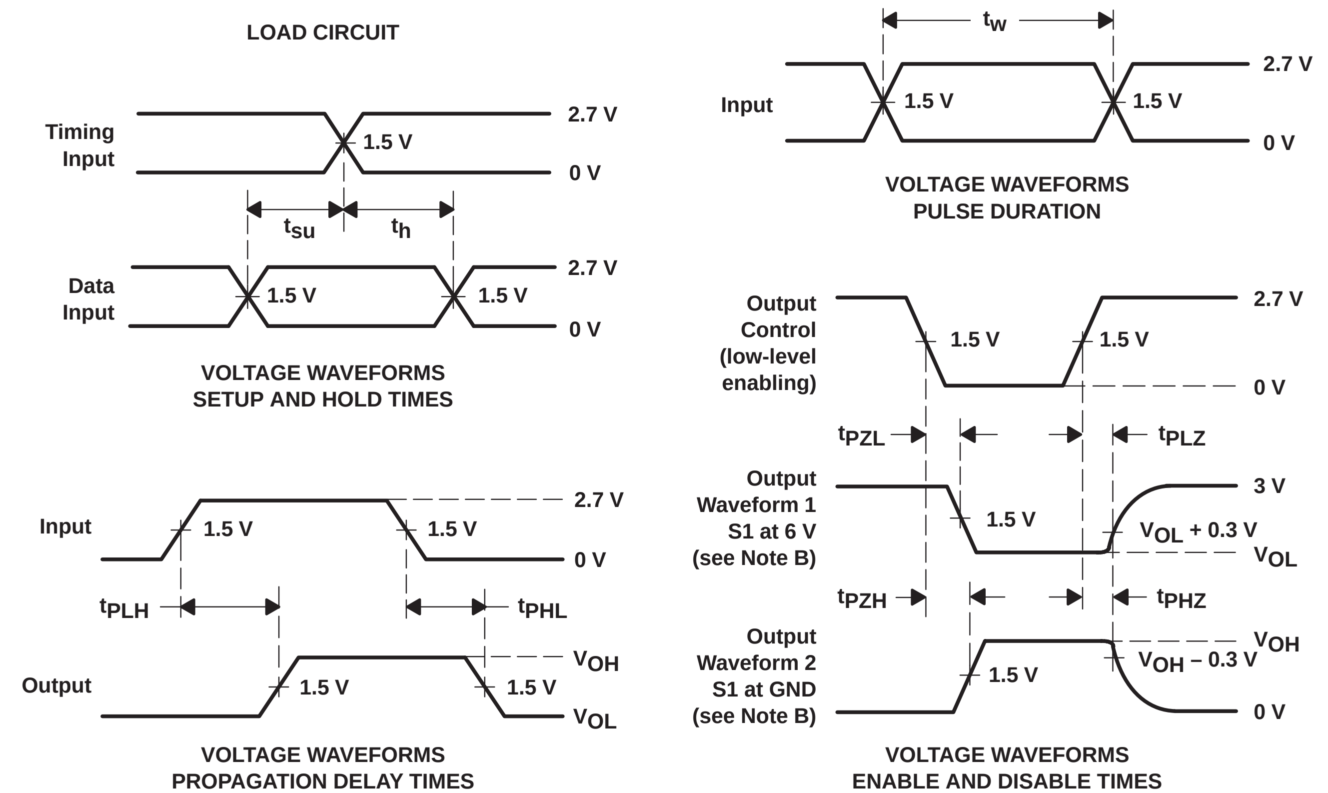
NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V



TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND



NOTES: A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.

D. The outputs are measured one at a time with one transition per measurement.

E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.

F. t_{PZL} and t_{PZH} are the same as t_{en}.

G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

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